ST3406SRG

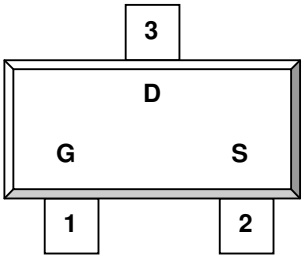
N Channel Enhancement Mode MOSFET

5.4A

DESCRIPTION

ST3406SRG is the N-Channel logic enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management, other battery powered circuits, and low in-line power loss are required. The product is in a very small outline surface mount package.

PIN CONFIGURATION
SOT-23

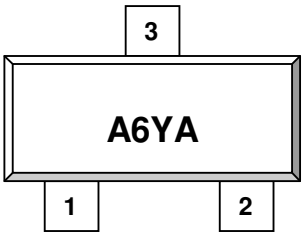


1.Gate 2.Source 3.Drain

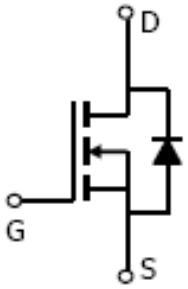
FEATURE

- 30V/5.4A, $R_{DS(ON)}$ = 26mΩ(Typ.) @V_{GS} = 10V
- 30V/4.6A, $R_{DS(ON)}$ = 38mΩ @V_{GS} = 4.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

PART MARKING
SOT-23



Y: Year Code A: Week Code



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ABSOULTE MAXIMUM RATINGS (Ta = 25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain CurrentTJ=150℃)	T_A=25℃ T_A=70℃	I_D	5.4 3.2	A
Pulsed Drain Current		I_{DM}	25	A
Continuous Source Current (Diode Conduction)		I_S	1.7	A
Power Dissipation	T_A=25℃ T_A=70℃	P_D	2.0 1.3	W
Operation Junction Temperature		T_J	150	℃
Storgae Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	90	℃/W

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ELECTRICAL CHARACTERISTICS (Ta = 25℃ Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS,I_D=250uA	1.0		3.0	V
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=24V,V_{GS}=0V			1	uA
		V_{DS}=24V,V_{GS}=0V T_J=55℃			10	
Drain-source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=4.0A V_{GS}=4.5V,I_D=3.6A		26 38		mΩ
Forward Transconductance	g_{fs}	V_{DS}=4.5V,I_D=5.4A		12		S
Diode Forward Voltage	V_{SD}	I_S=1.7A,V_{GS}=0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=15V V_{GS}=10V I_D≡6.7A		10	18	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			3.1		
Input Capacitance	C_{iss}	V_{DS}=15V V_{GS}=0V F=1MHz		450		pF
Output Capacitance	C_{oss}			240		
Reverse Transfer Capacitance	C_{rss}			38		
Turn-On Time	$t_{d(on)}$ tr	V_{DD}=15V R_L=15Ω I_D=1.0A V_{GEN}=10V R_G=6Ω		7	15	nS
				10	20	
Turn-Off Time	$t_{d(off)}$ tf			20	40	
				11	20	

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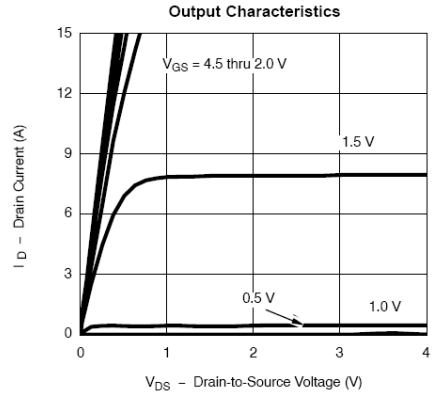
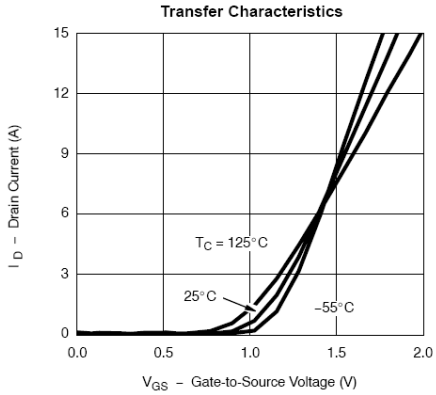
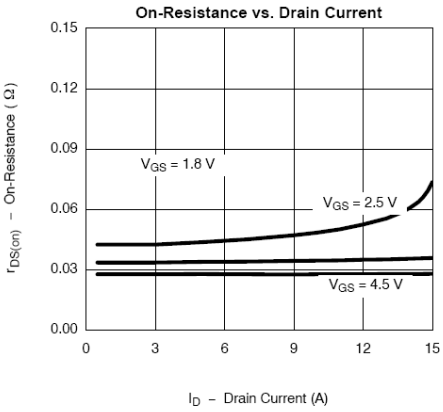
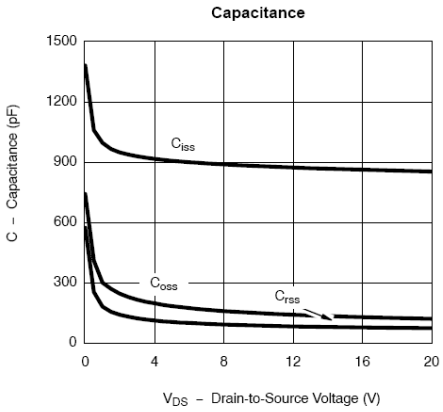
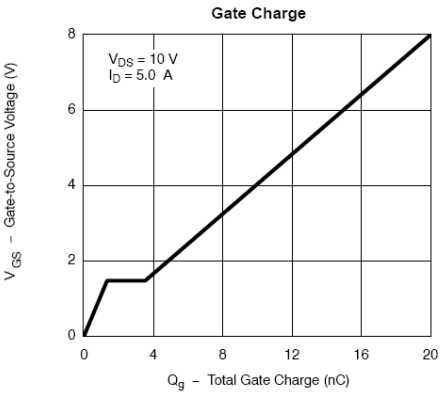
TYPICAL CHARACTERICTICS (25℃ unless otherwise noted)

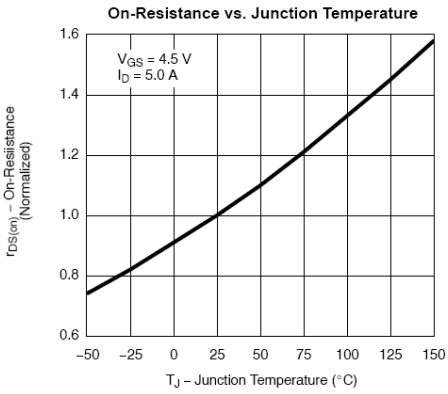












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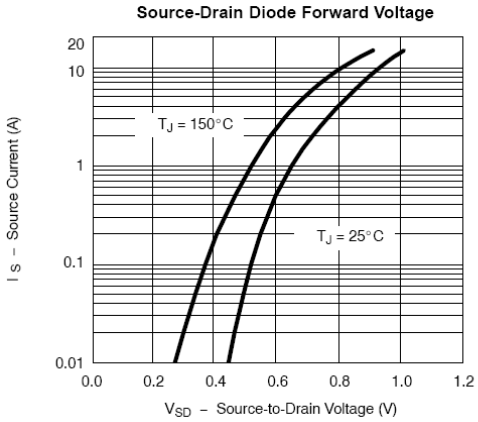

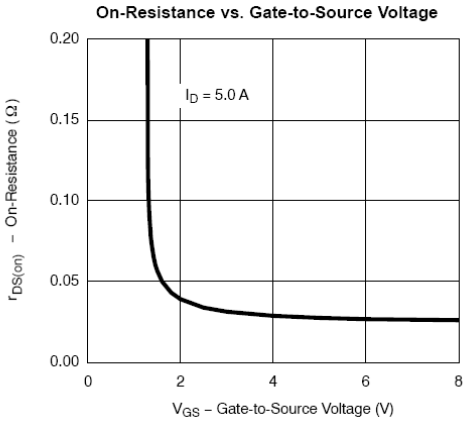

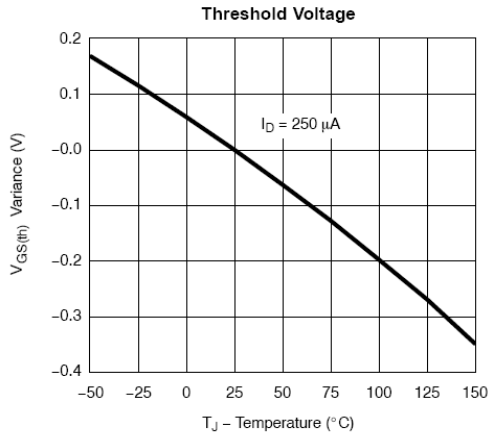

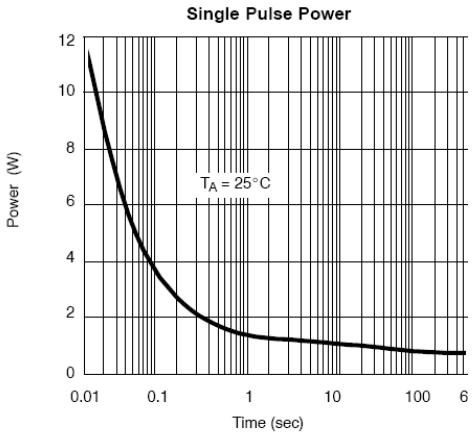

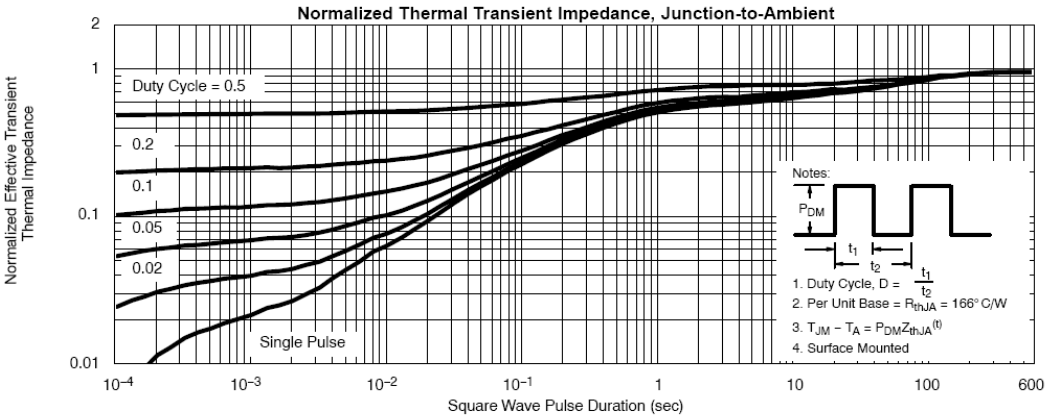

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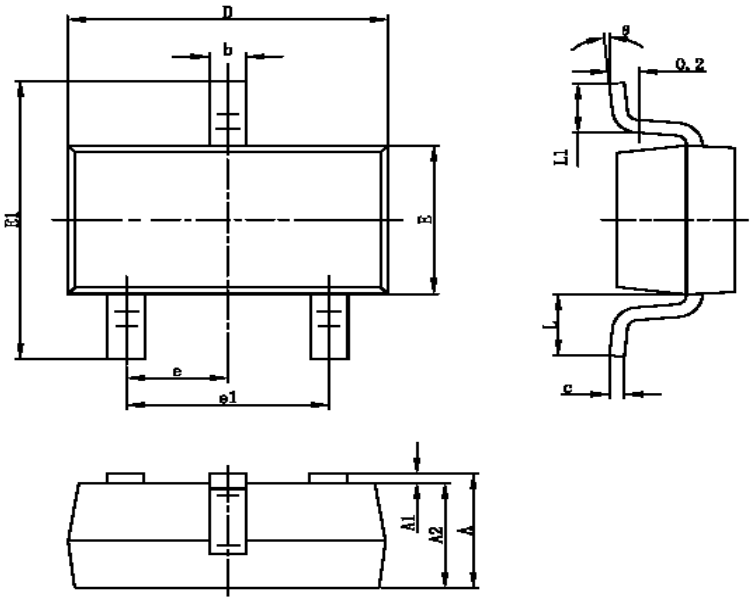
SOT-23 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.400	0.012	0.016
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.700REF		0.028REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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